

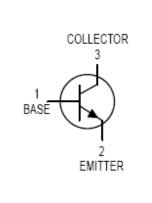
NPN General Purpose Transistor

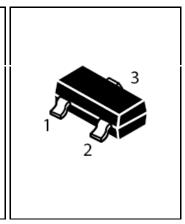
FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

MECHANICAL DATA

- Case: SOT-323 Plastic
- Case material: "Green" molding compound, UL flammability classification 94V-0, (No Br. Sb. Cl)
- Lead Free in RoHS 2002/95/EC Compliant





Maximum Ratings @ $T_A = 25^{\circ}C$

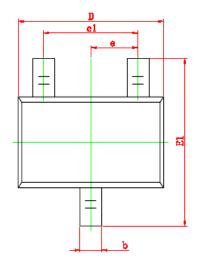
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	65	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I _C	100	mA
Collector Power Dissipation	Pc	150	mW
Junction Temperature	TJ	150	$^{\circ}\!\mathbb{C}$
Storage Temperature Range	T _{STG}	-55~+150	$^{\circ}\!\mathbb{C}$

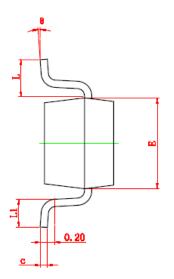
Electrical Characteristics @ T_A = 25°C unless otherwise specified

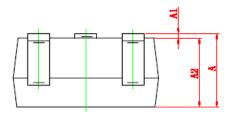
Characteristic	Test Condition		Symbol	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	$I_{C}=10\mu A, I_{E}=0$		V_{CBO}	80			V
Collector-emitter breakdown voltage	I _C =10mA,I _B =0		V_{CEO}	65			V
Emitter-base breakdown voltage	$I_E=1\mu A, I_C=0$		V_{EBO}	6			V
Collector-base cut-off current	V _{CB} =30V		I _{CBO}			15	nA
DC gurrant gain	V _{CE} =5V,I _C =10uA	AW BW	h _{FE1}		90 150		
DC current gain	V _{CE} =5V,I _C =2mA	AW BW	h _{FE2}	110 200		220 450	
Collector-emitter saturation voltage	I_{C} =10mA, I_{B} =0.5mA I_{C} =100mA, I_{B} =5mA		V _{CE} (sat)			0.25 0.6	V
Base-emitter saturation voltage	I _C =10mA,I _B =0.5mA I _C =100mA,I _B =5mA		V _{BE} (sat)		0.7 0.9		V
Base-emitter voltage	I_C =2mA, V_{CE} =5V I_C =10mA, V_{CE} =5V		V_{BE}	580	660	700 770	mV
Transition frequency	V _{CE} =5V,I _C =10mA, f=100MHz		f _T	100			MHz
Collector output capacitance	V _{CB} =10V,f=1MHz		C _{ob}			4.5	pF
Noise figure	VCE=5V,Ic=0.2mA, f=1KHz,RS=2KΩ Bandwidth=200Hz	BW	NF			10	dB

REV. 2, Jun-2012, KSNR04

SOT-323 Outline Dimension





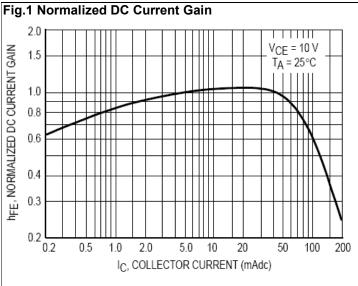


Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Device Marking:

Device P/N	Classification of h _{FE}	Marking code	
BC846AW	110-220	1A	
BC846BW	200-450	1B	

Electrical characteristic curves



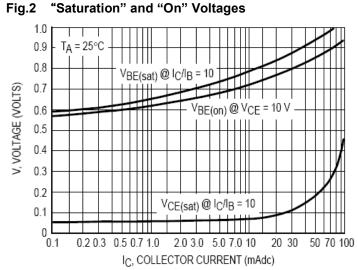


Fig.3 Collector Saturation Region

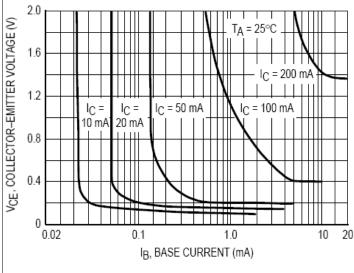


Fig.4 Base-Emitter Temperature Coefficient

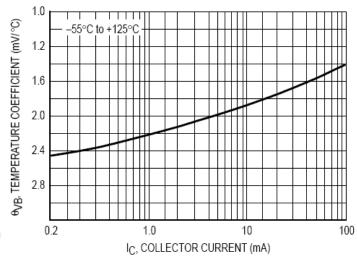


Fig.5 Capacitances

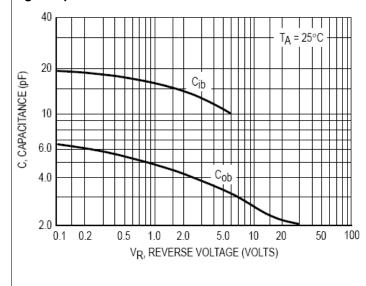
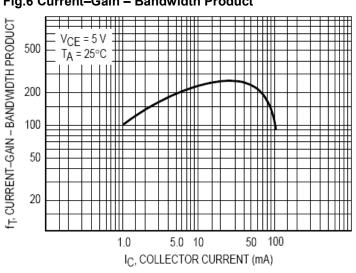


Fig.6 Current-Gain - Bandwidth Product





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